

Lecture 1 Dynamics of mesoscopic capacitors



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Mesoscopic Capacitor



Quantized charge relaxation resistance:

J. Gabelli, G. Fève, J.-M. Berroir, B. Plaçais, A. Cavanna, B. Etienne, Y. Jin, D.C. Glattli, SCIENCE 313, 499 (2006)

Quantized charge emission:

G.Fève, A. Mahé, J.-M.Berroir, T. Kottos, B.Plaçais, D. C., Glattli, A. Cavanna, B.Etienne, Y.Jin, SCIENCE 316, 1169 (2007)

Outline

Quantized charge relaxation resistance

- Scattering theory of mesoscopic capacitance
- The experiment
- Quantized charge relaxation resistance
- Role of coherence, quantum to classical crossover
- Role of interaction

Quantized charge emitter

- The experiment
- A Floquet (scattering) theory of non-linear response
- Accuracy of current quantization
- -Noise of the emitter

The mesoscopic capacitor

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Buttiker, Thomas, Prêtre, Phys. Lett. A 180, 364 (1993)



Classical versus quantum charge relaxation

8

Classical circuit



Dynamic potentials

Buttiker, Pretre, Thomas, Phys. Rev. Lett. 70, 4114 (1993)

Linear response to oscillating voltages

Distinguish:

potentials applied to terminals $dV_{\alpha}(t) = dV_{\alpha}(\omega)e^{-i\omega t}$ self-consistent electrostatic potential $dU(\omega, \mathbf{r})e^{-i\omega t}$

9



Dynamic external and internal response ¹⁰

Buttiker, Thomas, Pretre, Phys. Lett. A 180, 364 (1993)



External response

$$G^{ext}(\omega) = \frac{e^2}{h} \int dE \, Tr[1 - s^{\dagger}(E) \, s(E + \hbar\omega)] \, \frac{f(E) - f(E + \hbar\omega)}{\hbar\omega}$$

Internal response

 $G^{ext}(\omega) \, dV_1 + i\omega \,\Pi(\omega) \, dU = -i\omega \, C \, (dU - dV_2)$ Invariance under arbitrary potential shift $\longrightarrow i\omega \,\Pi = -G^{ext}$ $G^{-1}(\omega) = (-i\omega C)^{-1} + (G^{ext}(\omega))^{-1}$

Capacitance and Charge Relaxation

Buttiker, Thomas, Pretre, Phys. Lett. A180, 364 (1993) $G(\omega) = -i\omega C_{\mu} + \omega^2 C_{\mu}^2 R_q + \dots$ charge relaxation resistance electrochemical capacitance $C_{\mu}^{-1} = C^{-1} + (e^2 Tr[N])^{-1} \qquad R_q = \frac{h}{2e^2} \frac{Tr[N^{\dagger}N]}{(Tr[N])^2}$ Eigen channels of s; $\exp(i\phi_n)$; $n = 1, 2, , \longrightarrow$ $Tr[N] = \frac{1}{2\pi i} Tr[s^{\dagger} \frac{ds}{dE}] = \frac{1}{2\pi} \sum_{n} \frac{d\phi_n}{dE}$ $Tr[N^{\dagger}N] = \left(\frac{1}{2\pi}\right)^2 Tr\left[\frac{ds^{\dagger}}{dE}\frac{ds}{dE}\right] = \left(\frac{1}{2\pi}\right)^2 \sum \left(\frac{d\phi_n}{dE}\right)^2$ $R_q = \frac{h}{2e^2} \frac{\sum_n (d\phi_n/dE)^2}{(\sum_{n \neq m} d\phi_m/dE)^2}$

 $R_q = \frac{2e^2}{2e^2} \frac{(\sum_n d\phi_n/dE)^2}{(\sum_n d\phi_n/dE)^2}$ Universal for n =1; $R_q = \frac{h}{2e^2}$

Quantized charge relaxation resistances

Universal for n =1;

For k degenerate channels

Spin less electrons

Spin degenerate channel

Ideally coupled Carbon Nanotube

$$R_q = \frac{2e^2}{h} \frac{k}{k^2} = \frac{h}{2ke^2}$$
$$R_q = h/2e^2$$
$$R_q = h/4e^2$$

$$R_q = h/16e^2$$

 $B_{\alpha} = \frac{h}{\dots}$

Chaotic cavity coupled to two QPC (N channel) $R_q = \frac{h}{e^2} \frac{1}{N_1 + N_2}$ Brouwer and M. B., Europhys. Lett. 37, 441 (1997). Chaotic cavity coupled to two QPC (one channel) $P(R_q)$ Pedersen, van Langen, M. B., Phys. Rev. B 57, 1838 (1998).

Experimentalists model

Gabelli (thesis), Gabelli et al, Science 313, 499 (2006)

$$V=0 \begin{cases} & & & & \\ & & & & \\ & & & & \\ & & & \\ & &$$

density of states

$$N = \frac{1}{2\pi i} s^{\dagger} \frac{ds}{d\epsilon} = \frac{1}{2\pi i} s^{\dagger} \frac{ds}{d\phi} \frac{d\phi}{d\epsilon} = \frac{1}{2\pi} \frac{d\phi}{d\epsilon} \frac{1 - r^2}{1 - 2r\cos(\phi) + r^2}$$

assumption 1: uniform level spacing

$$\phi = 2\pi\epsilon/\Delta$$
assumption 2: voltage dependence of transmission through QPC
 $t^2 = 1/(1 + exp(-(V_{QPC} - V_0)/\Delta V_0))$

Mesoscopic Capacitor: Experiment

Gabelli, Feve, Berroir, Placais, Cavanna, Etienne, Jin, Glattli Science 313, 499 (2006).



 $\nu = 1.2GHz$ T = 100mK C = 4fF $C_{\mu} = 1fF$ B = 1.3T

Role of coherence

S. E. Nigg and M. Buttiker, (unpublished).

High-temperature limit

$$\frac{h}{2e^2} \xleftarrow{k_B T = 0} R_q = \frac{h}{2e^2} \frac{\int dE(-f'(E))\nu(E)^2}{\left(\int dE(-f'(E))\nu(E)\right)^2} \xrightarrow{k_B T \gg \Delta} \frac{\frac{h}{e^2} \frac{1 - \mathcal{T}}{\mathcal{T}}}{\frac{1 - \mathcal{T}}{R_s}} + \frac{h}{\frac{2e^2}{R_c}}$$

Dephasing and Inelastic scattering



 $U(\omega)$ Potential inside the cavity

Two dephasing models:

1) Voltage probe VP (dissipative)

$$I_{\phi}(\omega) = \int dE \, i_{\phi}(E,\omega) = 0, \quad \forall \omega$$

2) Dephasing probe **DP** (energy conserving)

$$i_{\phi}(E,\omega) = 0, \quad \forall E, \omega$$

Role of Coherence

S. E. Nigg and M. B. (unpublished).



Role of coherence

S. E. Nigg and M. B. (unpublished).



Role of charge quantization

 M. Buttiker and S. E. Nigg , Nanotechnolgy 18, 044029 (2007)
 Flensberg 1993

 [S. E. Nigg , R. Lopez and M. Buttiker, PRL 97, 206804 (2006)]
 Matveev 1995



Role of Interactions

S. E. Nigg, R. Lopez and M. Buttiker, PRL 97, 206804 (2006) Hartree-Fock

$$G^{ext}(\omega) = \frac{-i\omega}{2\pi} \int dE \frac{f(E+\omega) - f(E)}{\omega} tr[G^R(E+\omega) \Gamma G^A(E)].$$

$$kT = 0 \implies$$

$$\nu_{\sigma}(E) = \frac{1}{2\pi} Tr[D_{\sigma}(E)]; \qquad D_{\sigma}(E) = [G^{R}(E) \Gamma G^{A}(E)].$$

$$R_{q} = \frac{h}{2e^{2}} \frac{\sum_{\sigma} \nu_{\sigma}^{2}(E)}{(\sum_{\sigma} \nu_{\sigma}(E))^{2}}$$

For poarized spin channel $R_q = \frac{h}{2e^2}$ for "arbitrary" interactions!!

$$S(E) = 1 - itr[\Gamma G^{R}(E)]$$
$$tr(\Gamma A \Gamma B) = tr(\Gamma A)tr(\Gamma B)$$
$$G^{R} \Gamma G^{A} = i(G^{R} - G^{A}),$$
$$1/(2\pi i)S^{t} dS/dE = 1/2\pi tr[G^{R} \Gamma G^{A}]$$

From:ofer capacitors-ElecsoundDate:dimanche, 29. juillet 2007 14:41To:Markus.Buttiker@physics.unige.chSubject:offer capacitors

Hello, dear valued customer,

I am Jasmine from Elecsound. today I really want to recommend our capacitors to you. Elecsound is very strong in ta film capacitors and ceramic capacitors. all of our products are Lead free, good quality. fast lead time. If you need or and contact with us. tks

Tantalum capacitors

CA42 Dipped Tantalum capacitors CA45 SMD Tantalum Capacitors



Ceramic capacitors

Disc ceramic capacitors low voltage Disc ceramic capacitor high voltage AC Safe Ceramic Capacitor Y1 and Y2 Radial Multilayer ceramic capacitors Chip Multilayer ceramic capacitors 50V Chip Multilayer ceramic capacitors-high voltage Axial Multilayer ceramic capacitors 5mm ceramic trimmer capacitors 6mm ceramic trimmer capacitors

Film capacitors

CL20 METALLIZED POLYESTER FILM CAPACITOR-AXIAL CL21 Metallized polyester film capacitor CL23 Mini-Box metallized polyester film capacitor CBB11 Polypropylene film capacitor CBB20 Axial Mmetallized popypropylene film capacitor CBB21 Metallized polypropylene film capacitor

Quantized dynamic charge emission G.Fève, A. Mahé, J.-M.Berroir, T. Kottos, B.Plaçais, D. C., Glattli, A. Cavanna,

B.Etienne, Y.Jin, SCIENCE 316, 1169 (2007)



Quantized charge emission

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Floquet scattering theory of non-linear response

Moskalets, Samuelsson and M. B. cond-mat/0707.1927



Low frequency non-linear response

 $\Omega \tau \ll 1, \ \Omega = 2\pi/\mathcal{T}$

Instantaneous density of states (frozen density of states)

$$\nu(t, E) = \nu_0(E - eU(t)), \ \nu_0(E) = 1/(2\pi i)S_0^*(E)\partial S_0/\partial E \implies$$

$$I(t) = I_c(t) + I_d(t)$$

$$I_c(t) = e^2 \int dE \left(-\frac{\partial f_0}{\partial E}\right)\nu(t, E)\frac{\partial U}{\partial t}$$

$$I_d(t) = -e^2 \int dE \left(-\frac{\partial f_0}{\partial E}\right)\frac{h}{2}\frac{\partial \left[\nu^2(t, E)\frac{\partial U}{\partial t}\right]}{\partial t}$$

Differential capacitance and charge relaxation resistance

$$C_{\partial} = \partial Q / \partial U_{C} \qquad R_{\partial} = \partial U_{R} / \partial I \qquad U_{R} = U - U_{C}$$
$$C_{\partial}(t) = e^{2} \int dE \left(-\frac{\partial f_{0}}{\partial E} \right) \nu(t, E)$$
$$R_{\partial}(t) = \frac{h}{2e^{2}} \frac{\int dE \left(-\frac{\partial f_{0}}{\partial E} \right) \frac{\partial}{\partial t} \left(\nu^{2}(t, E) \frac{\partial U}{\partial t} \right)}{\int dE \left(-\frac{\partial f_{0}}{\partial E} \right) \nu(t, E) \int dE \left(-\frac{\partial f_{0}}{\partial E} \right) \frac{\partial}{\partial t} \left(\nu(t, E) \frac{\partial U}{\partial t} \right)}$$

Quantized charge emission

Slow driving

0

0

1

$$Q = \int_{t}^{T/2+t} dt I(t) \implies$$

$$Q = Q_{d}(U_{min}) - Q_{d}(U_{max}) + \mathcal{O}(\Omega\tau),$$

$$T \rightarrow 0, \ k_{B}T \rightarrow 0 \quad Q = en \text{ for } e\delta U = eU_{max} - eU_{min} = n\Delta$$

$$U(t) = U_{1} \cos(\Omega t)$$

$$= \text{transferred charge} - \text{from first harmonic only}$$

$$\mu \text{ resonant}$$

2 3 4 5 6

 $2eU_1 / \Delta$

Accuracy of quantization

$$\delta Q = Q - en, \ eu = e\delta U - n\Delta > 0$$

Finite temperature

$$\begin{split} \delta Q &= 2(\frac{eu}{k_B\theta}) \, \exp(-\frac{\Delta}{2k_B\theta}) \,, \; eu \to 0 \\ \delta Q &= -2\frac{\Delta - eu}{k_B\theta} \exp(-\frac{\Delta}{2k_B\theta}) \,, \; eu \to \Delta \end{split}$$

Finite transmission

$$\delta Q = \frac{Teu}{\pi^2 \Delta}, \ eu \to 0$$
$$\delta Q = -\frac{T(\Delta - eu)}{\pi^2 \Delta}, \ eu \to \Delta$$

optimization

 $\Omega\tau\ll T$

Square pulse of duration \mathcal{T}

Fève et al, Science 2007 for $k_BT >> \Delta$ or $e\delta U = n\Delta$ $I(t) = q/\tilde{\tau}e^{-(t-t_0)/\tilde{\tau}}, \quad q = e^2 \delta U/\Delta, \qquad \tilde{\tau} = (h/\Delta)(1/T - 1/2)$ **(a.u)** Floquet theory for $k_BT >> \Delta$ f=180MHz $I^{(nl)}(t) \rightarrow 0$, $I(t) = \frac{e^2 \delta U}{h} T R^{N(t)}, \quad k_B T \gg \Delta , \quad \text{for} \qquad \mathcal{T} > t - t_0 > 0 ,$. Temps (ns) $N(t) = [[(t - t_0)/\tau]]$, piecewise constant long time $t - t_0 \gg 0$, $I(t) \sim e^{-(t-t_0)/\tau_D}$, with $\tau_D = h/(\Delta \ln(1/R))$ nearly $\tau_D \approx \tilde{\tau}$, Floquet theory for $k_BT \ll \Delta$ $I^{(nl)}(t) \neq 0 \; ,$

Summary

Quantized charge relaxation resistance

For a single spin-polarized channel, self-consistent scattering theory predicts a universal charge relaxation resistance of half a resistance quantum h

$$R_q = \frac{n}{2e^2}$$

A seminal experiment by Gabelli et al. supports this prediction Role of dephasing Role of charge quantization Role of interactions

Quantized dynamic charge emission and absorption

$$Im I_f = 2e f$$

Demonstrated in an experiment by Fève et al.

Accuracy Noise